

## The 15th QiR 2017 Submission 182

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Submission 182	
Title	Effect of Ge mole fraction on current, voltage and electric field characteristics of high doping nanoscale Si1-xGex/Si p-n diode.
Abstract Submission:	 (Dec 01, 13:20 GMT)
Full paper:	 (Mar 31, 03:30 GMT)
Revised Paper (Camera Ready):	 (Jun 08, 10:22 GMT)
Copyright Form:	 (Jun 08, 10:22 GMT)
Registration Form and payment:	 (Jun 30, 12:09 GMT)
Author keywords	SiGe Si Ge mole fraction current voltage electric field p-n diode high doping nanoscale
EasyChair keyphrases	ge mole fraction (649), electric field (233), high doping nanoscale si1 xgex (232), mole fraction (205), maximum electric field (158), reverse bias (120), reverse bias voltage (95), nanoscale si1 xgex (63), electric field characteristic (63), energy band diagram (63), maximum electric field value (60), high doping (60), energy gap (50), bias voltage (50), forward bias (50), lower energy (50), cogenda visualcad (50), electrical engineering politeknik negeri (40), si ge diode (40), band tunneling (40)
Topics	Intl. Sym. on Electrical and Computer Eng.
Submitted	Dec 01, 13:20 GMT
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Authors							
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### Reviews

Review 1	
Writing	The abstract is too long, please concise the abstract.
Paper content	Research background, Novelty, and Analysis are clear.
Overall evaluation	The paper will be accepted if some minor revisions is corrected.

Review 2	
Writing	The paper is well written in scientific English standard, although there are some misspell such as acceptor and soon. Author summarize several published paper in the background however it is not clearly stated the position of the proposed paper. Authors should explain the reason of doing the research. Is it just confirming the previous research results or there are something new with the paper. Author mentioned that Si1-xGex acts as acceptor while Si as donor. I think authors miss understand about definition of acceptor and donor with anode and cathode. if it is correct that Si1-xGex and Si are acceptor and donor respectively, then what is the substrate of the materials? it is also not clear how authors claim high doping while substrate were not known.
Paper content	In the discussion, author focus on the effect of Ge mode fraction to the current. From the results, I think it is clear that Ge affect the threshold voltage. the current might be the same for different Ge fraction for different voltage.  Band diagram is very important to explain the behavior and authors already drew the band diagram however it is also not clear how authors draw the band diagram.
Overall evaluation	If authors can clarify the confusion, we can accept the paper

Review 3	
Writing	Paper structure follows the standard scientific paper. The English needs improvement.
Paper content	<ul style="list-style-type: none"> <li>- Abstract is too long.</li> <li>- Background is still unclear.</li> <li>- Novelty is still unclear.</li> <li>- The analysis of the data is good enough.</li> </ul>
Overall evaluation	This paper presents the effect of Ge mole fraction on high doping nanoscale SiGe/Si diode. Event several points above are needed to be improved, this paper can be accepted.

## Talk 182

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## Talk

Title	Effect of Ge mole fraction on current, voltage and electric field characteristics of high doping nanoscale Si1-xGex/Si p-n diode.
Authors	Anak Agung Ngurah Made Narottama and <a href="#">Anak Agung Ngurah Gde Sapteka</a>
Abstract	
Author keywords	SiGe Si Ge mole fraction current voltage electric field p-n diode high doping nanoscale
Number	182
Two-session	no
Session	not assigned
Time	unknown
Duration (minutes)	15
Presenter	unknown
Scheduling remarks	

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